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Key Features of Renesas Electronics' New Low-Latency DRAM

Product Name	μ PD48576109	μ PD48576118	μ PD48576209	μ PD48576218	μ PD48576236
Capacity	576Mb				
I/O Type	Separate I/O			Common I/O	
Bit Width	x9	x18	x9	x18	x36
No. of Banks	8				
Burst Length	2 / 4 / 8				
Supply Voltage	VDD	1.8V +/- 0.1V			
	VDDQ	1.5V~1.8V +/-0.1V			
	VEXT	2.5V +0.13V / -0.12V			
Operating Frequency	533MHz / 400MHz / 300MHz				
Latency	tRC	Minimum 15ns			
	tRL	= tRC			
	tWL	tRL + 1 Cycle			
Termination	1/2 VDDQ				
Package	144-pin BGA (11 x 18.5mm)				